

TOSHIBA TRANSISTOR SILICON NPN TRIPLE DIFFUSED TYPE

2SD798

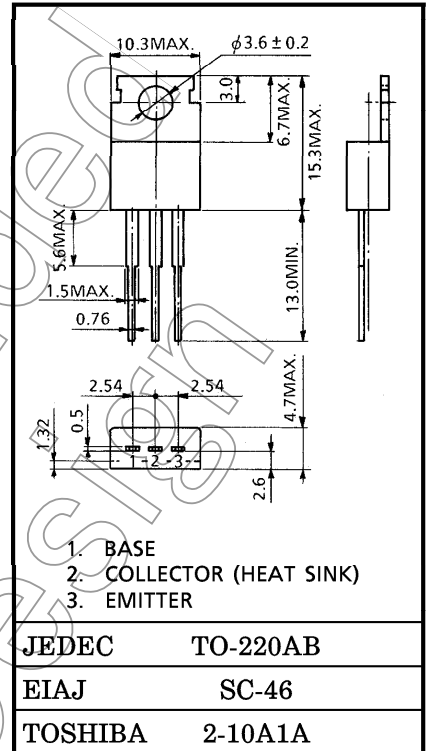
IGNITER APPLICATIONS

HIGH VOLTAGE SWITCHING APPLICATIONS

INDUSTRIAL APPLICATIONS

Unit in mm

- High DC Current Gain : $h_{FE} = 1500$ (Min.) ($V_{CE} = 2V, I_C = 2A$)



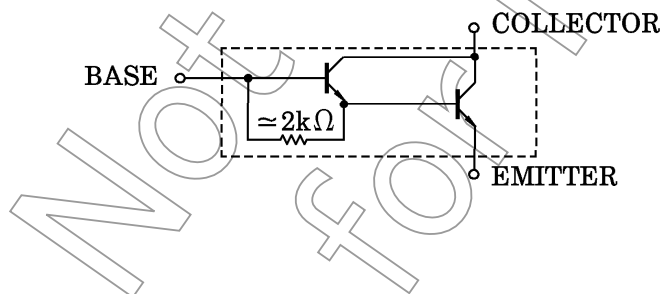
MAXIMUM RATINGS ($T_a = 25^\circ C$)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CB0}	600	V
Collector-Emitter Voltage	V_{CEO}	300	V
Emitter-Base Voltage	V_{EB0}	5	V
Collector Current	I_C	6	A
Base Current	I_B	1	A
Collector Power Dissipation ($T_c = 25^\circ C$)	P_C	30	W
Junction Temperature	T_j	150	$^\circ C$
Storage Temperature Range	T_{stg}	-55~150	$^\circ C$

Weight : 1.9g

Mounting Kit No. AC75

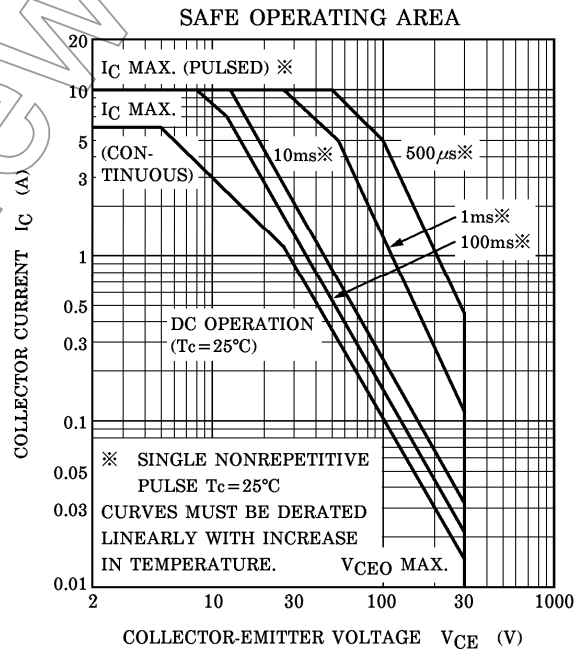
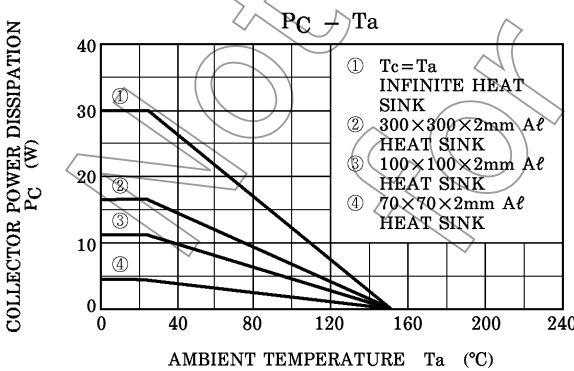
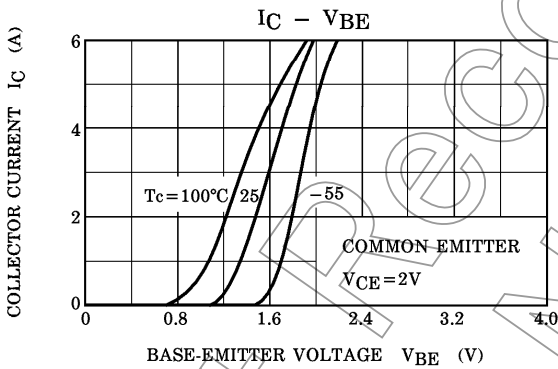
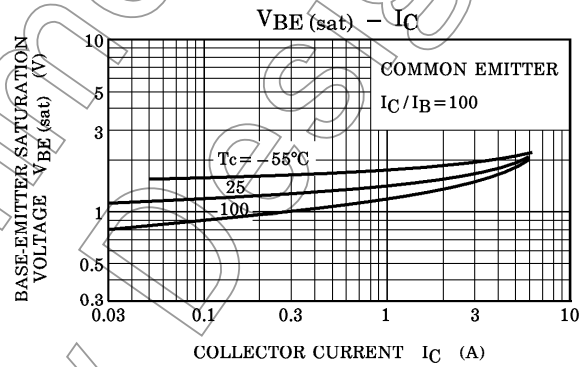
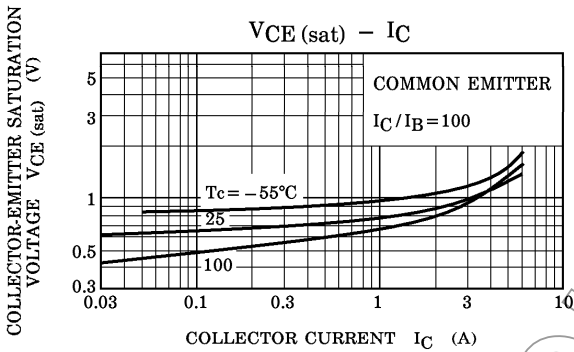
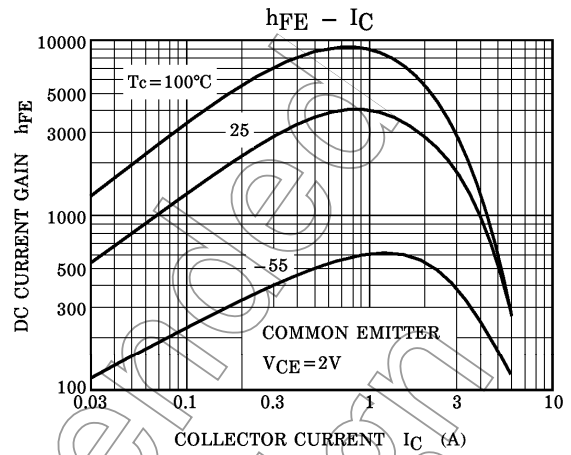
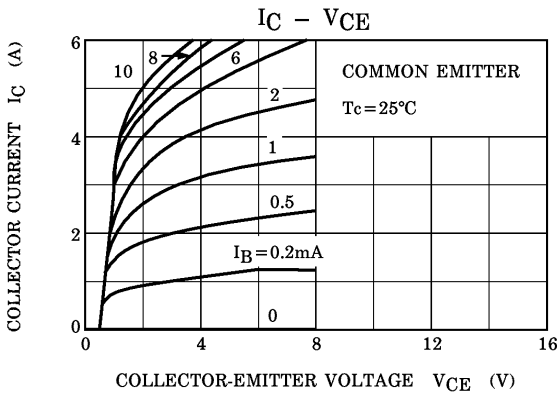
EQUIVALENT CIRCUIT



ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current		ICBO	V _{CB} = 600V, I _E = 0	—	—	0.5	mA
Emitter Cut-off Current		IEBO	V _{EB} = 5V, I _C = 0	—	—	0.5	mA
Collector-Emitter Sustaining Voltage		V _{CEO} (SUS)	I _C = 0.5A, L = 40mH	300	—	—	V
DC Current Gain		h _{FE} (1)	V _{CE} = 2V, I _C = 2A	1500	—	—	
		h _{FE} (2)	V _{CE} = 2V, I _C = 4A	200	—	—	
Collector-Emitter Saturation Voltage		V _{CE} (sat)	I _C = 4A, I _B = 0.04A	—	—	2.0	V
Base-Emitter Saturation Voltage		V _{BE} (sat)	I _C = 4A, I _B = 0.04A	—	—	2.5	V
Collector Output Capacitance		C _{ob}	V _{CB} = 50V, I _E = 0, f = 1MHz	—	35	—	pF
Switching Time	Turn-on Time	t _{on}	<p>IN-PUT 20 μs</p> <p>OUTPUT</p> <p>I_{B1}</p> <p>I_{B2}</p> <p>V_{CC} ≅ 100V</p> <p>DUTY CYCLE ≅ 1%</p>	—	1	—	μs
	Storage Time	t _{stg}		—	8	—	
	Fall Time	t _f		I _{B1} = -I _{B2} = 0.04A, DUTY CYCLE ≅ 1%	—	5	

Not Recommended for New Design



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